

Silicon NPN Power Transistors

2SC2625

DESCRIPTION

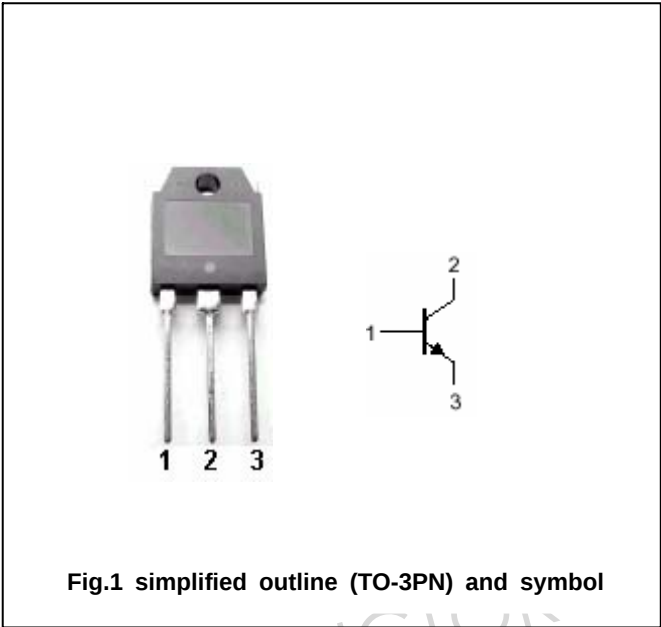
- With TO-3PN package
- High voltage,high speed switching
- High reliability

APPLICATIONS

- Switching regulators
- Ultrasonic generators
- High frequency inverters
- General purpose power amplifiers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Tc=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	450	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		10	A
I_B	Base current		3	A
P_C	Collector power dissipation	$T_C=25$	80	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-C}$	Thermal resistance junction to case	1.55	/W

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA ; I_B=0$	400			V
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=1A ; I_B=0$	400			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA ; I_E=0$	450			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=0.1mA ; I_C=0$	7			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=4A ; I_B=0.8A$			1.2	V
V_{BEsat}	Emitter-base saturation voltage	$I_C=4A ; I_B=0.8A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=450V ; I_E=0$			1.0	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=7V ; I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=4A ; V_{CE}=5V$	10			

Switching times

t_{on}	Turn-on time	$I_C=7.5A ; I_{B1}=-I_{B2}=1.5A$ $R_L=20\Omega , P_w=20\mu s$ Duty $\leq 2\%$			1.0	μs
t_s	Storage time				2.0	μs
t_f	Fall time				1.0	μs

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PACKAGE OUTLINE

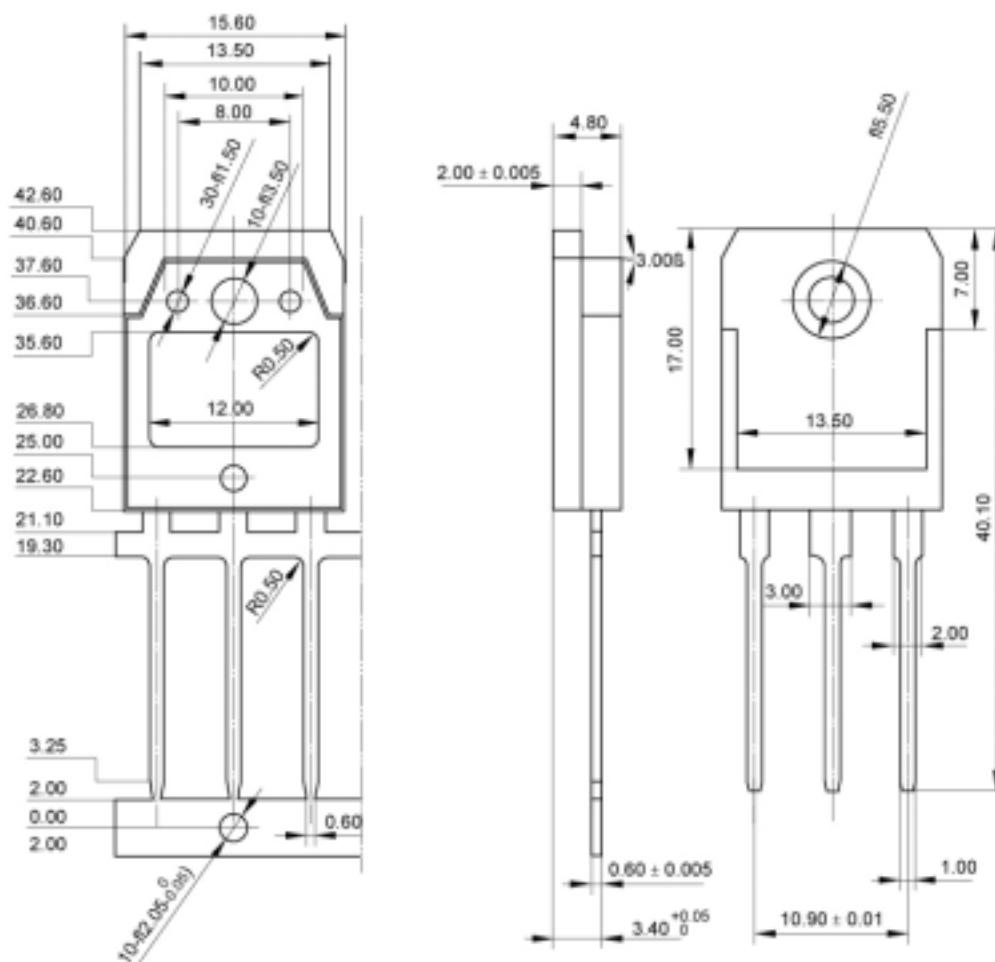


Fig.2 outline dimensions

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